

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1630	(438/197).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 12:50
S2	0	438/197.ccls. and ((single or mono) adj crystal adj (layer or film)) and island and depress\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:44
S3	18	"438"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and island and depress\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 09:26
S4	39	"257"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and island and depress\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 09:19
S5	42	semiconductor and ((single or mono) adj crystal adj (layer or film)) and island and depress\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 09:19
S6	2	("20050230761").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 09:30
S7	1	("6764936").PN.	USPAT	OR	OFF	2006/08/21 10:13
S8	1	("20060131663").PN.	US-PGPUB; USPAT	OR	OFF	2006/08/21 10:14
S9	1	("20050173766").PN.	US-PGPUB; USPAT	OR	OFF	2006/08/21 10:14

## EAST Search History

S10	41	("5043043"   "5206983"   "5286335"   "5327033"   "5453405"   "5534466"   "5549785"   "5587343"   "5589082"   "5637539"   "5638946"   "5644177"   "5645684"   "5646464"   "5662771"   "5717631"   "5789264"   "5839722"   "5842106"   "5851851"   "5866281"   "5867202"   "5881598"   "5908719"   "5914507"   "5929542"   "5943155"   "5949571"   "5959338"   "5963788"   "5971355"   "5972780"   "6028331"   "6078100"   "6228275"   "6238946"   "6265781"   "6287885"   "6331444"   "6388279"   "6417021").PN.	US-PGPUB; USPAT; USOCR.	OR	ON	2006/08/21 11:21
S11	2	("20050167673").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:38
S12	2	("6133105").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/08/21 13:51
S13	6499	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:58
S14	242	(semiconductor adj substrate) with (trench or opening or open or hole or aperture or groove) with ((high adj density adj plasma) or ("HDP"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:57
S15	2078	(semiconductor adj substrate) and ((trench or opening or open or hole or aperture or groove) with ((high adj density adj plasma) or ("HDP")))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:57

## EAST Search History

S16	101	(semiconductor adj substrate) and ((trench or opening or open or hole or aperture or groove) near ((high adj density adj plasma) or ("HDP"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 13:57
S17	88	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and (etch\$4 adj back) and ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:00
S18	1	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and ((etch\$4 adj back) with ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:01
S19	4	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and ((etch\$4 adj back) same ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:01
S20	88	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and ((etch\$4 adj back) and ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2"))))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:14
S21	23	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and ((etch\$4 adj back) and ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2")))) and (("FSG") or (florinat\$3 adj (silicon or ("Si")) adj glass))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:19
S22	23	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and ((high adj density adj plasma) or ("HDP")) and ((etch\$4 adj back) and ("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2")))) and (("FSG") or (fluorinat\$3 adj (silicon or ("Si")) adj glass))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/22 13:56

## EAST Search History

S23	0	(semiconductor adj substrate) and (trench or opening or open or hole or aperture or groove) and (((high adj density adj plasma) or ("HDP")) adj (oxide or insulat\$4 or dielectric) adj (layer or film)) and ((etch\$4 adj back) and (("C.sub.2 F.sub.6") and (oxygen or ("O.sub.2")))) and (("FSG") or (fluorinat\$3 adj (silicon or ("Si")) adj glass))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/08/21 14:23
S24	3	((("6562651") or ("7071111") or ("20030080395")).PN.	US-PGPUB; USPAT	OR	OFF	2006/08/22 14:25
S25	2063	(438/149).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:07
S28	26	438/197.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:51
S29	1556	"438"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:26
S30	2306	"257"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:46
S31	3389	semiconductor and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:25
S32	131	(semiconductor and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:45

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S33	54	(semiconductor and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)).clm.	US-PGPUB	OR	ON	2007/01/17 13:45
S34	2101	"257"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3) and @ad<="20040916"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:25
S35	828	(438/164).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 13:47
S36	89	438/197,149,164.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:51
S37	89	438/197,149,164.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 13:52
S38	502	"257"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3) and @ad<="20040916" and island	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:25
S39	655	semiconductor and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3) and island	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:25
S40	336	"438"/\$.ccls. and ((single or mono) adj crystal adj (layer or film)) and (separat\$4 or depress\$5 or remov\$3) and island and @ad<="20040916"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/17 14:26

## EAST Search History

S41	1881	(438/689).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:08
S42	99	(438/484).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:08
S43	185	(438/489).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:08
S44	72	(438/490).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:09
S45	828	(438/164).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:10
S46	983	(438/458).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/17 15:28